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MC74VHC50

Hex Buffer

The MC74VHC50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V}$ (Max)
- These Devices are Pb-Free and are RoHS Compliant

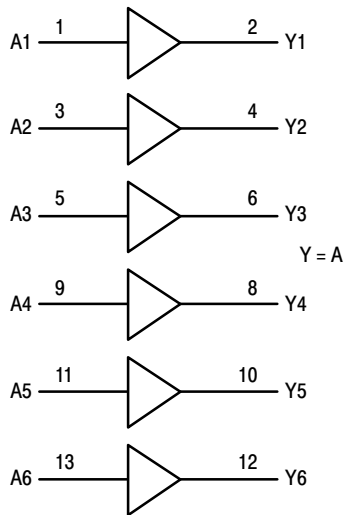


Figure 1. Logic Diagram

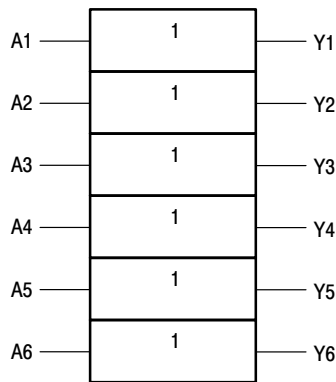
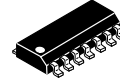


Figure 2. Logic Symbol

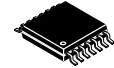


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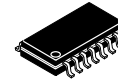
<http://onsemi.com>



14-LEAD SOIC
D SUFFIX
CASE 751A

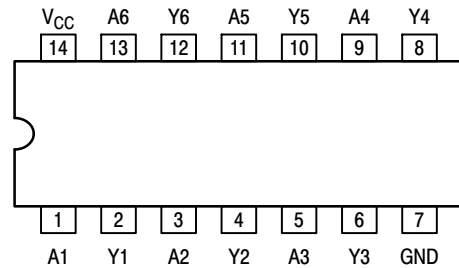


14-LEAD TSSOP
DT SUFFIX
CASE 948G



14-LEAD SOIC EIAJ
M SUFFIX
CASE 965

PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

FUNCTION TABLE

A Input	Y Output
L	L
H	H

ORDERING INFORMATION

Device	Package	Shipping
MC74VHC50DG	SOIC	55 Units/Rail
MC74VHC50MG	SOIC EIAJ	50 Units/Rail
MC74VHC50DR2G	SOIC	2500 Units/T&R
MC74VHC50DTR2G	TSSOP	2500 Units/T&R

MC74VHC50

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	- 0.5 to + 7.0	V
V _{IN}	DC Input Voltage	- 0.5 to + 7.0	V
V _{OUT}	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current V _I < GND	- 20	mA
I _{OK}	DC Output Diode Current V _O < GND	± 20	mA
I _{OUT}	DC Output Sink Current	± 25	mA
I _{CC}	DC Supply Current per Supply Pin	± 50	mA
T _{STG}	Storage Temperature Range	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature under Bias	+ 150	°C
θ _{JA}	Thermal Resistance (Note 1) SOIC TSSOP	125 170	°C/W
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30 to 35	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 5)	± 300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	5.5	V
V _I	Input Voltage (Note 6)	0	5.5	V
V _O	Output Voltage (HIGH or LOW State)	0	V _{CC}	V
T _A	Operating Free-Air Temperature	- 55	+ 125	°C
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 3.0 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

6. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

NOTE: The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

MC74VHC50

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.0 3.15 3.85			1.5 2.0 3.15 3.85		1.5 2.0 3.15 3.85	V	
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4	V	
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66	V	
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36	0.44 0.44		0.52 0.52	V	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS (C_{load} = 50 pF, Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Y	V _{CC} = 3.0 ± 0.3 V C _L = 15 pF C _L = 50 pF		5.0 7.5	7.1 10.6		8.5 12.0		10.0 14.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		3.8 5.3	5.5 7.5		6.5 8.5		8.0 10.0	
C _{IN}	Maximum Input Capacitance			4	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 7)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		18		

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0 ns, C_L = 50 pF, V_{CC} = 5.0 V)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.8	1.0	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.8	-1.0	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

MC74VHC50

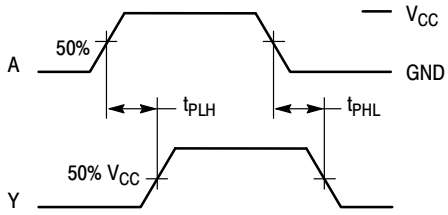
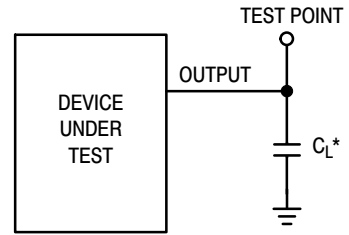


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

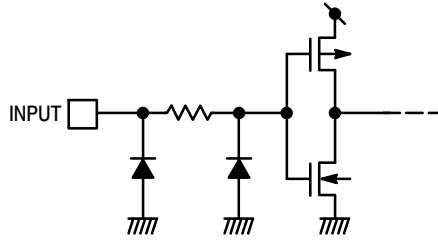
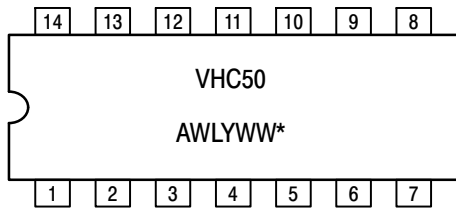
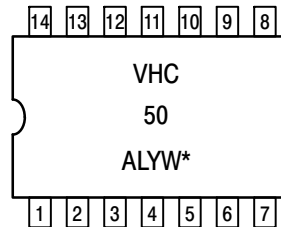


Figure 5. Input Equivalent Circuit

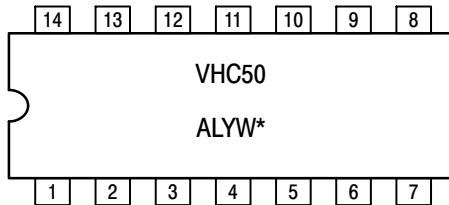
MARKING DIAGRAMS (Top View)



14-LEAD SOIC
D SUFFIX
CASE 751A



14-LEAD TSSOP
DT SUFFIX
CASE 948G



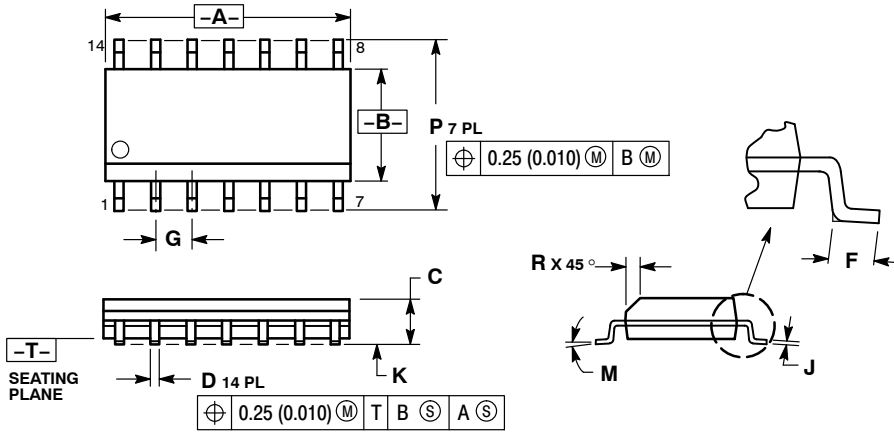
14-LEAD SOIC EIAJ
M SUFFIX
CASE 965

*See Applications Note #AND8004/D for date code and traceability information.

MC74VHC50

PACKAGE DIMENSIONS

SOIC-14
CASE 751A-03
ISSUE J

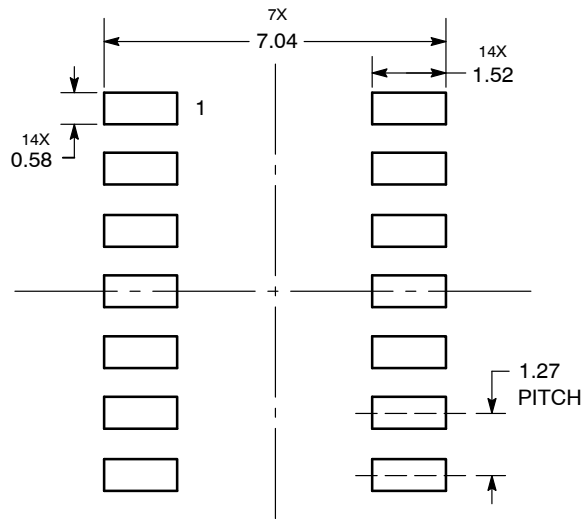


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT

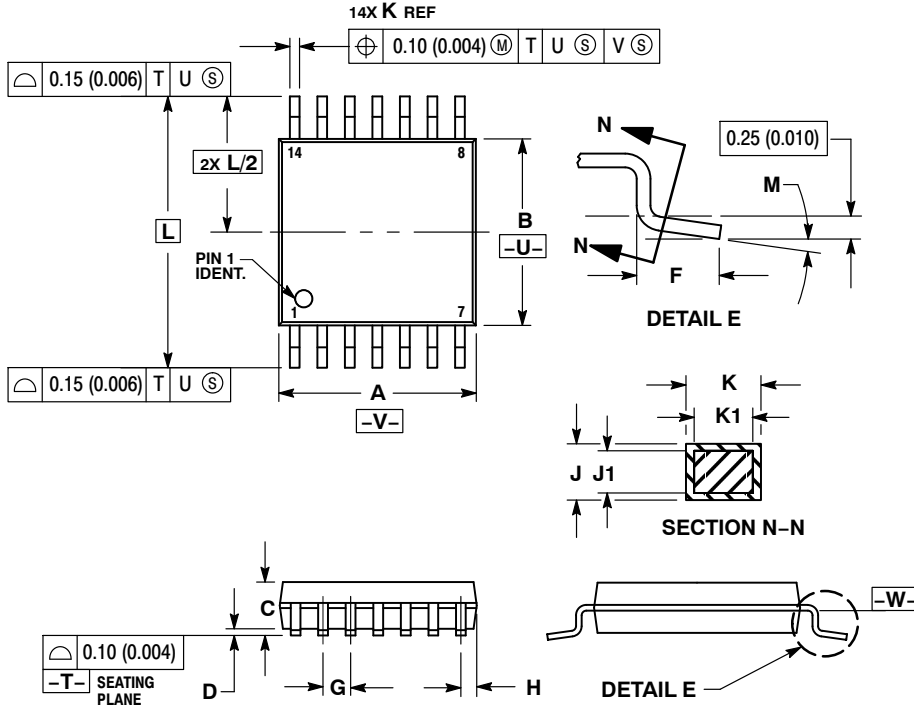


DIMENSIONS: MILLIMETERS

MC74VHC50

PACKAGE DIMENSIONS

TSSOP-14
CASE 948G-01
ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -V-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT

